

**AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions, and listings, of claims in the present application.

**Listing of Claims:**

1. **(Currently Amended)** A method of manufacturing a phase shift mask blank comprising a transparent substrate and at least one layer of phase shift film thereon, and further comprising a chromium-base light-shielding film being formed on the phase shift film,

said method comprising the steps of forming the phase shift film on the ~~substrate and surface treating~~ substrate, oxidizing an outermost surface of the phase shift film with ozone water having 1 to 50 ppm of ozone dissolved therein; therein, and forming the chromium-base light-shielding film on the phase shift film which has been surface treated with the ozone water.

2. **(Currently Amended)** A method of manufacturing a phase shift mask blank comprising a transparent substrate and at least one layer of phase shift film thereon, and further comprising a chromium-base light-shielding film being formed on the phase shift film,

said method comprising the steps of forming the phase shift film of a metal silicide oxide, metal silicide nitride or metal silicide oxynitride on the ~~substrate and surface treating~~ substrate, oxidizing an outermost surface of the phase shift film with ozone water having 1 to 50 ppm of ozone dissolved therein; therein, and forming the chromium-base light-shielding film on the phase shift film which has been surface treated with the ozone water.

3. **(Currently Amended)** A method of manufacturing a phase shift mask blank comprising a transparent substrate and at least one layer of phase shift film thereon, and further comprising a chromium-base light-shielding film being formed on the phase shift film,

said method comprising the steps of forming the phase shift film of a molybdenum silicide oxide, molybdenum silicide nitride or molybdenum silicide oxynitride on the ~~substrate~~ and surface-treating substrate, oxidizing an outermost of the phase shift film with ozone water having 1 to 50 ppm of ozone dissolved therein; therein, and forming the chromium-base light-shielding film on the phase shift film which has been surface treated with the ozone water.

4. **(Original)** The method of manufacturing a phase shift mask blank of claim 1 wherein said phase shift film changes the phase of exposure light passing therethrough by  $180 \pm 5$  degrees and has a transmittance of 3 to 40%.

5. **(Original)** A method of manufacturing a phase shift mask, comprising the steps of forming by photolithography a patterned resist film on the phase shift film in the phase shift mask blank obtained by the method of claim 1,

etching away the portions of the phase shift mask which are uncovered with the resist film, and

thereafter, removing the resist film.

6. **(Canceled)**

7. **(Previously Presented)** The method of manufacturing a phase shift mask blank of claim 1, wherein the ozone water has 5 to 50 ppm of ozone dissolved therein.

8. **(Canceled)**

9. **(Previously Presented)** The method of manufacturing a phase shift mask blank of claim 2, wherein the ozone water has 5 to 50 ppm of ozone dissolved therein.

10. **(Previously Presented)** The method of manufacturing a phase shift mask blank of claim 2, wherein said phase shift film changes the phase of exposure light passing therethrough by  $180 \pm 5$  degrees and has a transmittance of 3 to 40%.

11. **(Previously Presented)** A method of manufacturing a phase shift mask, comprising the steps of

forming by photolithography a patterned resist film on the phase shift film in the phase shift mask blank obtained by the method of claim 2,

etching away the portions of the phase shift mask which are uncovered with the resist film, and

thereafter, removing the resist film.

12. **(Canceled)**

13. **(Previously Presented)** The method of manufacturing a phase shift mask blank of claim 3, wherein the ozone water has 5 to 50 ppm of ozone dissolved therein.

14. **(Previously Presented)** The method of manufacturing a phase shift mask blank of claim 3, wherein said phase shift film changes the phase of exposure light passing therethrough by  $180 \pm 5$  degrees and has a transmittance of 3 to 40%.

15. **(Previously Presented)** A method of manufacturing a phase shift mask, comprising the steps of

forming by photolithography a patterned resist film on the phase shift film in the phase shift mask blank obtained by the method of claim 3,

etching away the portions of the phase shift mask which are uncovered with the resist film, and

thereafter, removing the resist film.

16. **(New)** The method of manufacturing a phase shift mask blank of claim 1, wherein said at least one layer of phase shift film is formed on said substrate by a reactive sputtering technique.

17. (New) The method of manufacturing a phase shift mask blank of claim 2, wherein said at least one layer of phase shift film is formed on said substrate by a reactive sputtering technique.

18. (New) The method of manufacturing a phase shift mask blank of claim 3, wherein said at least one layer of phase shift film is formed on said substrate by a reactive sputtering technique.